New Release

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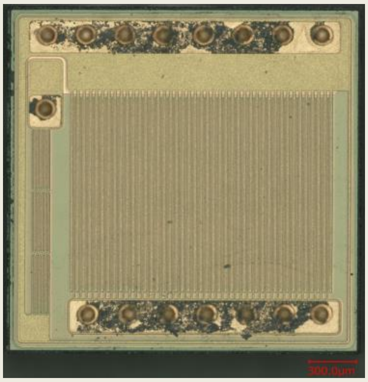
Panasonic GaN Power HEMT PGA26E19BA

Analysis Reports of Structure, Package, Process, ESD protection element

- Jun 2016, LTEC Corporation released the structure, Package, Process and ESD protection element analysis reports of Panasonic GaN Power HEMT PGA26E19BA.

Package



Die

- PGA26E19BA is designed for high power switching applications is normally-off GaN-based HEMT.

  Feature

  1. Vdds=600V, DC Id=10A, On-resistance per unit area $(\mathrm{RonxA})_i$=292mΩ x mm^2
     (Previous model PGA26C09DV $(\mathrm{RonxA})_i$=486mΩ x mm^2)
  2. Top Metal is Au. (Top Metal of PGA26C09DV is Cu rewiring of 2 layers.)
  3. DFN Package (PGA26C09DV TO-220 Package)
  4. Gate ESD protection element is embedded in the chip.

  ※ We sell the structure report of previous model PGA26C09DV.

- These reports reveal the details of Transistor, Package, technology, ESD protection element.

Structure Analysis Report	**$4,000**
Package Analysis Report	**$1,500**
Process Analysis Report	**$2,000**
ESD protection element Analysis Report	**$1,500**

Structure Analysis Report

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